Preferred Devices

Complementary Silicon Power Transistors

These series of plastic, silicon NPN and PNP power transistors can be used as general purpose power amplification and switching such as output or driver stages in applications such as switching regulators, converters and power amplifiers.

Features

- Pb-Free Package is Available
- Low Collector–Emitter Saturation Voltage V_{CE(sat)} = 1.0 V (Max) @ 8.0 A
- Fast Switching Speeds
- Complementary Pairs Simplifies Designs

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage D44H8, D45H8 D44H11, D45H11	V _{CEO}	60 80	Vdc
Emitter Base Voltage	V _{EB}	5.0	Vdc
Collector Current - Continuous - Peak (Note 1)	I _C	10 20	Adc
Total Power Dissipation @ T _C = 25°C @ T _A = 25°C	P _D	50 2.0	W
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2.5	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	°C/W
Maximum Lead Temperature for Soldering Purposes: 1/8" from Case for 5 Seconds	T _L	275	°C

^{1.} Pulse Width \leq 6.0 ms, Duty Cycle \leq 50%.



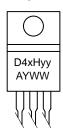
ON Semiconductor®

http://onsemi.com

10 A COMPLEMENTARY SILICON POWER TRANSISTORS 60, 80 V



MARKING DIAGRAM



x = 4 or 5yy = 8 or 11

TO-220AB CASE 221A STYLE 1

A = Assembly Location

Y = Year WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping [†]
D44H8	TO-220	50 Units/Rail
D44H11	TO-220	50 Units/Rail
D45H8	TO-220	50 Units/Rail
D45H8G	TO-220 (Pb-Free)	50 Units/Rail
D45H11	TO-220	50 Units/Rail

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

	Characteristic	Symbol	Min	Max	Unit
DC Current Gain (V _{CE} = 1.0 Vdc, I _C = 2.0 Adc)		h _{FE}			-
	D44H8, 11 D45H8, 11		20 40	_	
$(V_{CE} = 1.0 \text{ Vdc}, I_{C} = 4.0 \text{ Adc})$	D44H8, 11 D45H8, 11		20 40	-	

	,					
ELECTRICAL CHARACTERISTICS (T _C = 25°C unless of	herwise noted)					
Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Collector Cutoff Current (V _{CE} = Rated V _{CEO} , V _{BE} = 0)		I _{CES}	-	_	10	μΑ
Emitter Cutoff Current (V _{EB} = 5.0 Vdc)		I _{EBO}	-	_	100	μА
ON CHARACTERISTICS						
Collector–Emitter Saturation Voltage ($I_C = 8.0 \text{ Adc}$, $I_B = 0.4 \text{ Adc}$) ($I_C = 8.0 \text{ Adc}$, $I_B = 0.8 \text{ Adc}$)	D44H/D45H8, 11 D44H	V _{CE(sat)}	_ _	_ _	1.0 1.0	Vdc
Base–Emitter Saturation Voltage $(I_C = 8.0 \text{ Adc}, I_B = 0.8 \text{ Adc})$		V _{BE(sat)}	-	-	1.5	Vdc
DYNAMIC CHARACTERISTICS						
Collector Capacitance (V _{CB} = 10 Vdc, f _{test} = 1.0 MHz)	D44H Series D45H Series	C _{cb}	_ _	130 230	_ _	pF
Gain Bandwidth Product (I _C = 0.5 Adc, V _{CE} = 10 Vdc, f = 20 MHz)	D44H Series D45H Series	f⊤	- -	50 40	- -	MHz
SWITCHING TIMES						
Delay and Rise Times (I _C = 5.0 Adc, I _{B1} = 0.5 Adc)	D44H Series D45H Series	t _d + t _r	_ _	300 135	- -	ns
Storage Time $(I_C = 5.0 \text{ Adc}, I_{B1} = I_{B2} = 0.5 \text{ Adc})$	D44H Series D45H Series	t _S	_ _	500 500	- -	ns
Fall Time (I _C = 5.0 Adc, I _{B1} = 102 = 0.5 Adc)	D44H Series D45H Series	t _f	_ _	140 100	_ _	ns

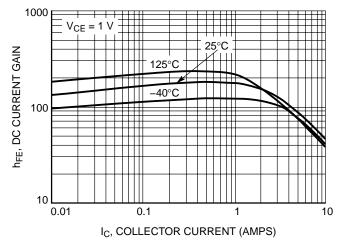


Figure 1. D44H11 DC Current Gain

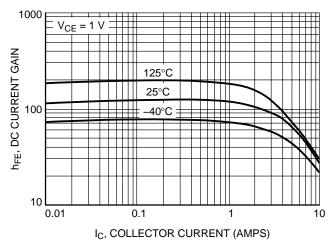


Figure 2. D45H11 DC Current Gain

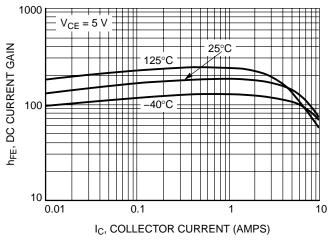


Figure 3. D44H11 DC Current Gain

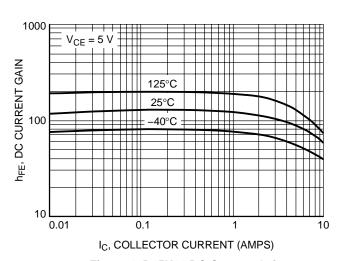


Figure 4. D45H11 DC Current Gain

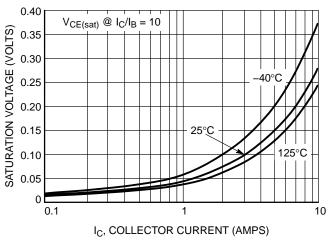


Figure 5. D44H11 ON-Voltage

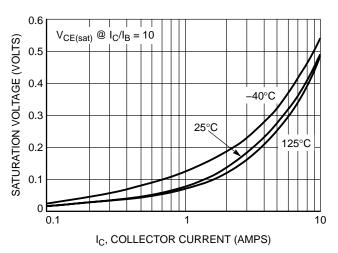
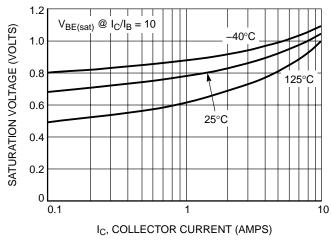


Figure 6. D45H11 ON-Voltage

1.4

1.2

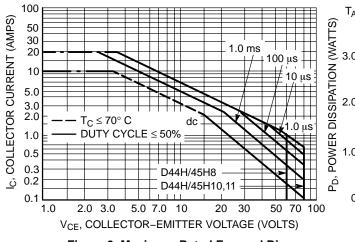
 $V_{BE(sat)} @ I_C/I_B = 10$



SATURATION VOLTAGE (VOLTS) -40°C 1.0 0.8 125°C 0.6 25°C 0.4 0.2 0 0.1 10 IC, COLLECTOR CURRENT (AMPS)

Figure 7. D44H11 ON-Voltage

Figure 8. D45H11 ON-Voltage



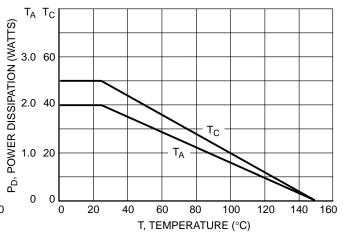


Figure 9. Maximum Rated Forward Bias Safe Operating Area

Figure 10. Power Derating

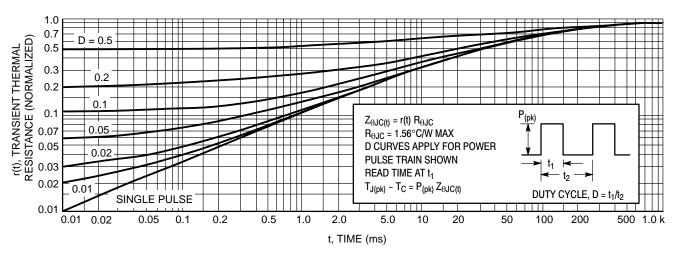
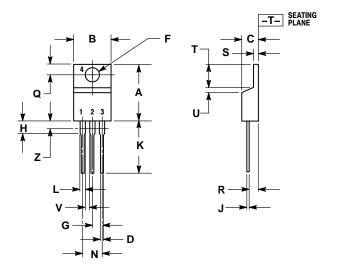


Figure 11. Thermal Response

PACKAGE DIMENSIONS

TO-220 **PLASTIC** CASE 221A-09 **ISSUE AA**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.405	9.66	10.28
С	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
Н	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080		2.04

- STYLE 1:
 PIN 1. BASE
 2. COLLECTOR
 3. EMITTER
 4. COLLECTOR

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